

# IRFU13N20DPBF-VB Datasheet

## N-Channel 200V (D-S) MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
200	0.056 at $V_{GS} = 10$ V	25
	0.070 at $V_{GS} = 6$ V	23

### FEATURES

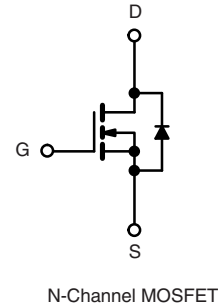
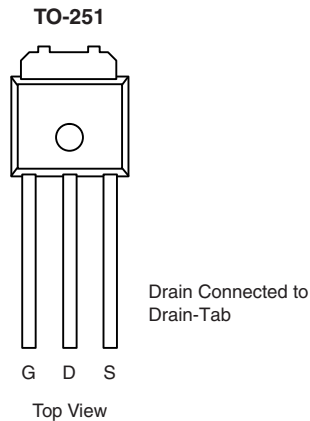
- Trench Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized
- 100 %  $R_g$  Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT

### APPLICATIONS

- Primary Side Switch



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	200	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175$ °C) <sup>b</sup>	$I_D$	25	A
		17	
Pulsed Drain Current	$I_{DM}$	60	
Continuous Source Current (Diode Conduction)	$I_S$	19	
Avalanche Current	$I_{AS}$	25	
Single Pulse Avalanche Energy	$E_{AS}$	18	mJ
Maximum Power Dissipation	$P_D$	145 <sup>b</sup>	W
		3.5 <sup>a</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 175	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	15	18	°C/W
		40	50	
Junction-to-Case (Drain)	$R_{thJC}$	0.85	1.1	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. See SOA curve for voltage derating.

SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	200			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2		4	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
		V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	40			A
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A		0.056		Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A, T <sub>J</sub> = 125 °C		0.130		
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A, T <sub>J</sub> = 175 °C		0.260		
		V <sub>GS</sub> = 6 V, I <sub>D</sub> = 5 A		0.070		
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 19 A		35		S
Dynamic <sup>a</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, F = 1 MHz		2400		pF
Output Capacitance	C <sub>oss</sub>			280		
Reverse Transfer Capacitance	C <sub>rss</sub>			180		
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 19 A		40		nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			10		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			15		
Gate Resistance	R <sub>g</sub>		0.5		2.9	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 100 V, R <sub>L</sub> = 5.2 Ω I <sub>D</sub> ≡ 19 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 2.5 Ω		15	25	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			50	75	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			30	45	
Fall Time <sup>c</sup>	t <sub>f</sub>			60	90	
Source-Drain Diode Ratings and Characteristics (T <sub>C</sub> = 25 °C)						
Pulsed Current	I <sub>SM</sub>				50	A
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>F</sub> = 19 A, V <sub>GS</sub> = 0 V		0.9	1.5	V
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 19 A, di/dt = 100 A/μs		180	250	ns

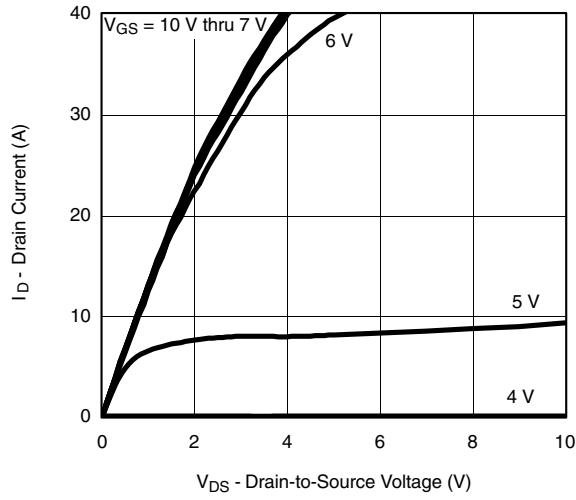
Notes:

a. Guaranteed by design, not subject to production testing.

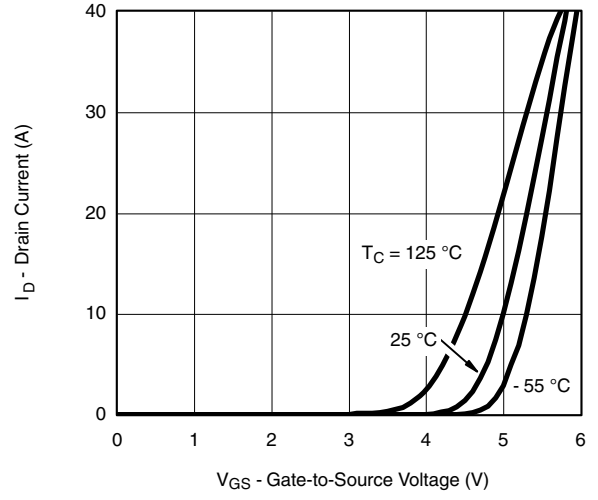
b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

c. Independent of operating temperature.

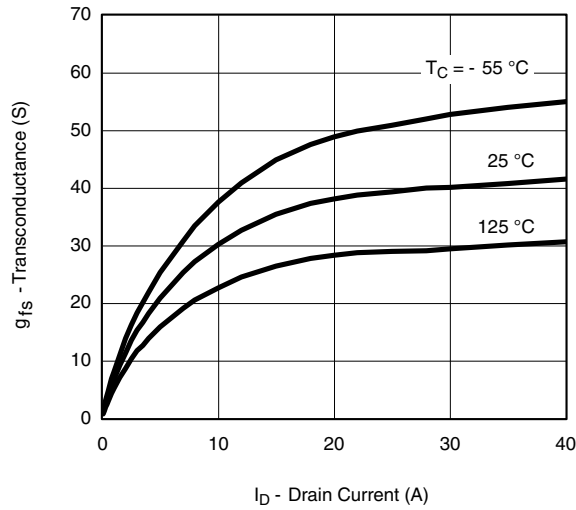
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



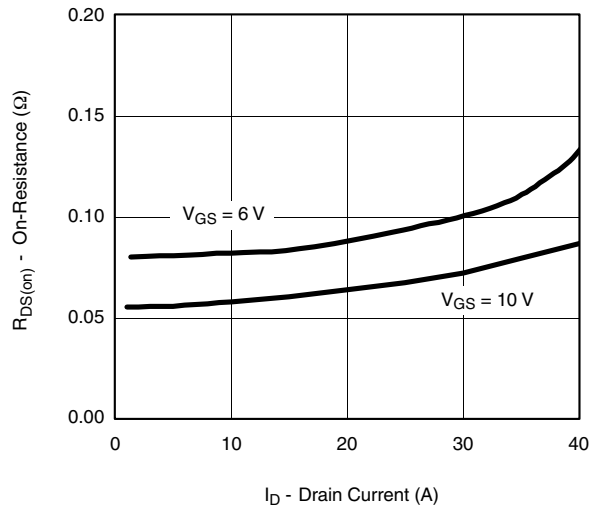
**Output Characteristics**



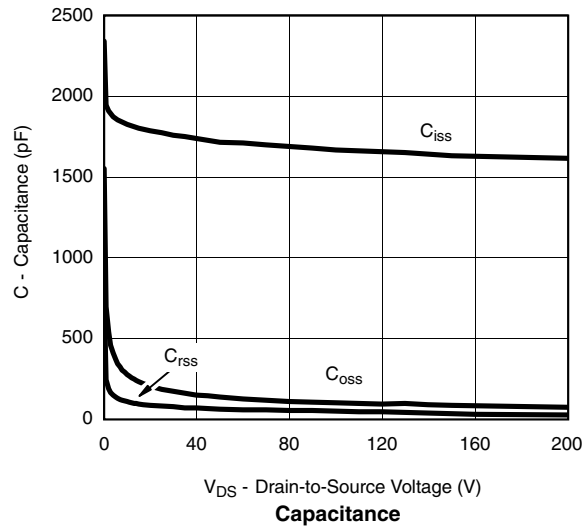
**Transfer Characteristics**



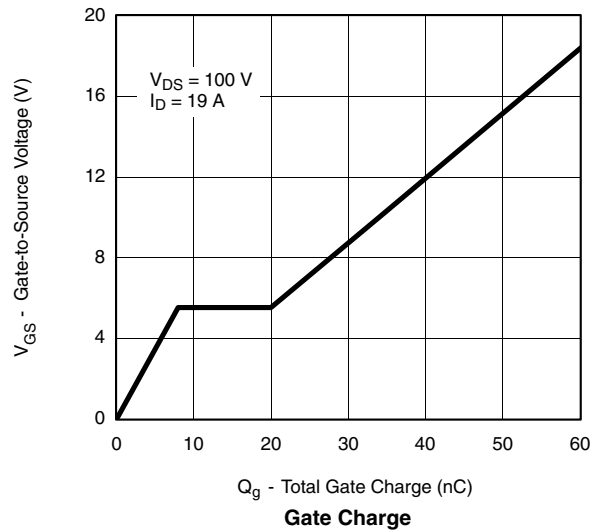
**Transconductance**



**On-Resistance vs. Drain Current**

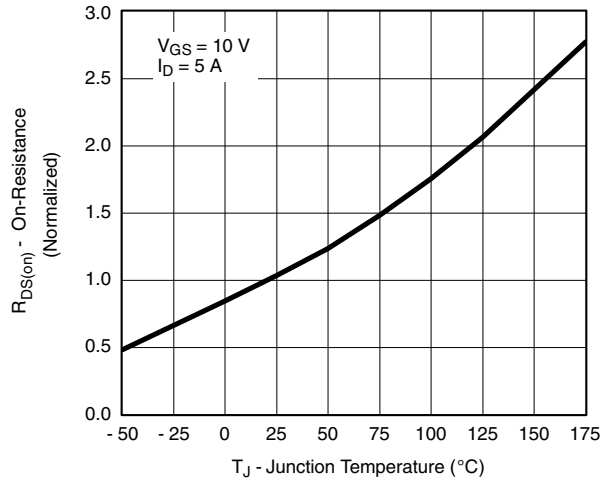


**Capacitance**

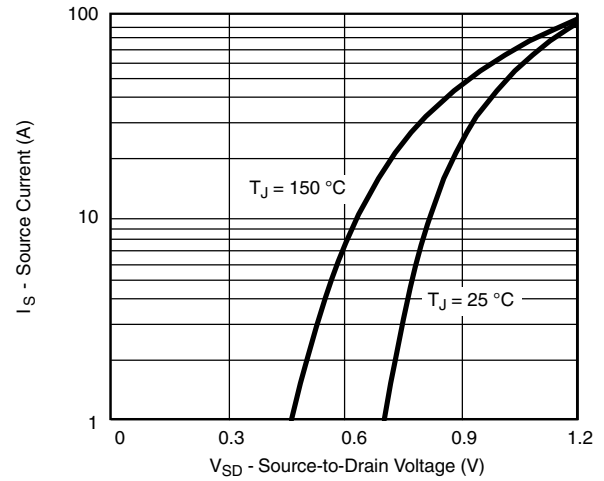


**Gate Charge**

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

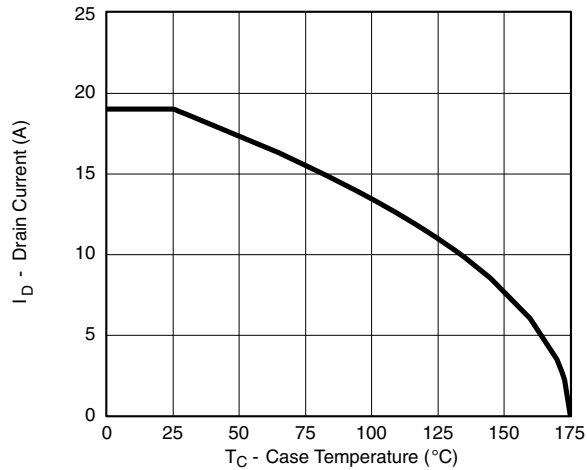


On-Resistance vs. Junction Temperature

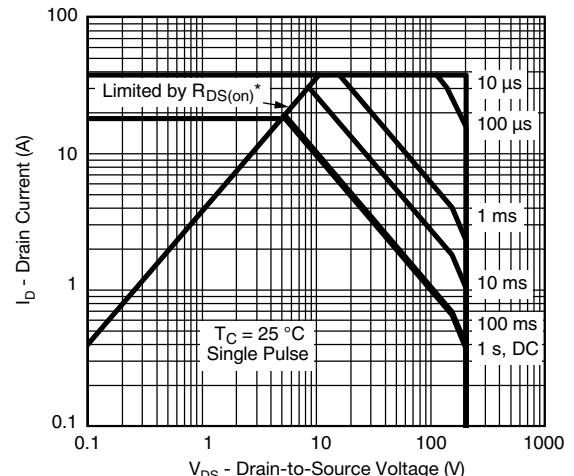


Source-Drain Diode Forward Voltage

## THERMAL RATINGS

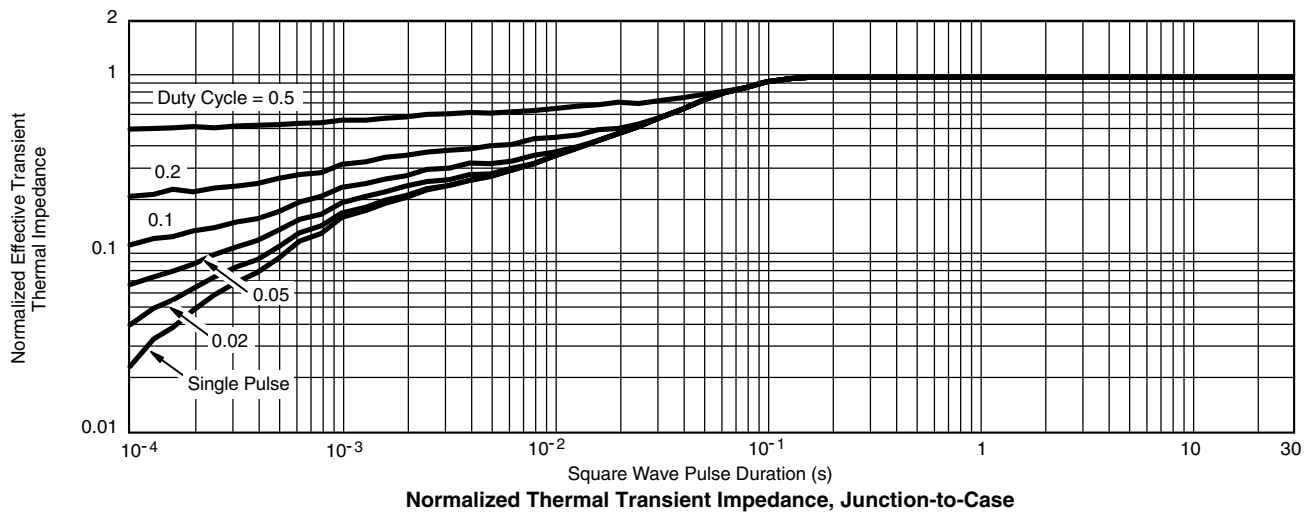


Maximum Avalanche Drain Current vs. Case Temperature



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

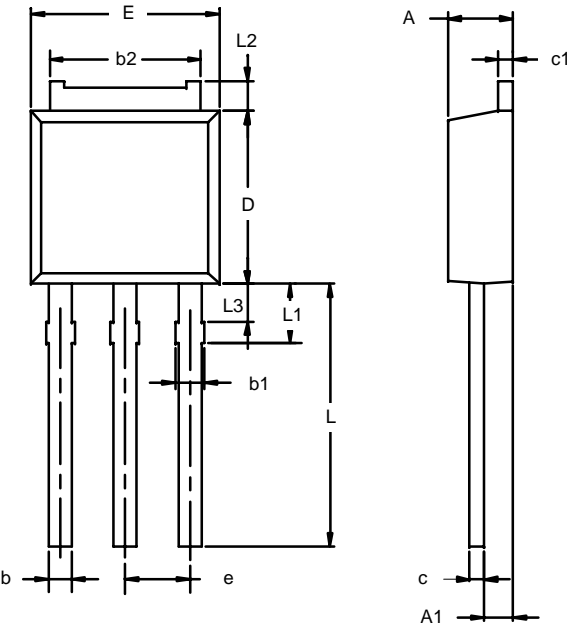
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

# IRFU13N20DPBF-VB

## TO-251AA



Note: Dimension L3 is for reference only.

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
<b>A</b>	2.21	2.38	0.087	0.094
<b>A1</b>	0.89	1.14	0.035	0.045
<b>b</b>	0.71	0.89	0.028	0.035
<b>b1</b>	0.76	1.14	0.030	0.045
<b>b2</b>	5.23	5.43	0.206	0.214
<b>c</b>	0.46	0.58	0.018	0.023
<b>c1</b>	0.46	0.58	0.018	0.023
<b>D</b>	5.97	6.22	0.235	0.245
<b>E</b>	6.48	6.73	0.255	0.265
<b>e</b>	2.28 BSC		0.090 BSC	
<b>L</b>	3.89	9.53	0.153	0.375
<b>L1</b>	1.91	2.28	0.075	0.090
<b>L2</b>	0.89	1.27	0.035	0.050
<b>L3</b>	1.15	1.52	0.045	0.060

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